

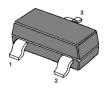
MMBTSC4226 NPN Silicon Epitaxial Planar Transistor

High Frequency Low Noise Amplifier.

The transistor is subdivided into three groups, Q, R and S, according to its DC current gain.

Features:

- Low Noise
 NF=1.2dB TYP. @ f=1GHz, V_{CE}=3V, I_C=7mA
- High Gain S_{21e}^{1} = 9.0dB TYP. @ f=1GHz, V_{CE} =3V, I_{C} =7mA



1.Base 2.Emitter 3.Collector SOT-23 Plastic Package

Description:

The MMBTSC4226 is a low supply voltage transistor designed for VHF, UHF low noise amplifier.

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	20	V
Collector Emitter Voltage	V _{CEO}	12	V
Emitter Base Voltage	V _{EBO}	3	V
Collector Current	Ic	100	mA
Total Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _S	-65 to +150	°C



Characteristics at T_{amb}=25 °C

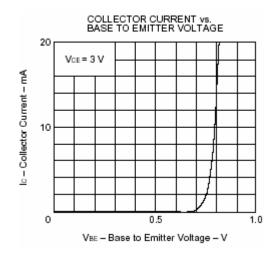
Parameter	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V _{CE} =3V, I _C =7mA					
Current Gain Group Q	h _{FE}	50	-	100	-
R	h _{FE}	80	-	160	-
S	h _{FE}	125	-	250	-
Collector Cutoff Current					
at V _{CB} =10V	I _{CBO}	-	-	1.0	μA
Emitter Cutoff Current					
at V _{EB} =1V	I _{EBO}	-	-	1.0	μA
Gain Bandwidth Product					
at V _{CE} =3V, I _C =7mA	f _T	3.0	4.5	-	GHz
Feed back Capacitance 1)					
at V _{CE} =3V, f=1MHz	C_{re}	-	0.7	1.5	pF
Insertion Power Gain					
at V _{CE} =3V, I _C =7mA, f=1GHz	S _{21e} ²	7	9	-	dB
Noise Figure					
at V _{CE} =3V, I _C =7mA, f=1GHz	NF	-	1.2	2.5	dB

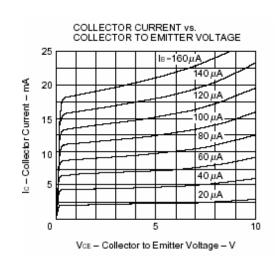
¹⁾ Measured with 3 terminal bridge, Emitter and case should be grounded.

Classification of h_{FE}

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RANK	Q	R	S
MARKING	R23	R24	R25
h _{FE}	50 ~100	80 ~160	125 ~250

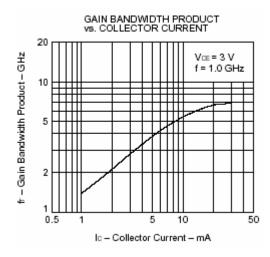
Typical Characteristics

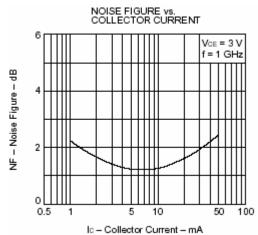


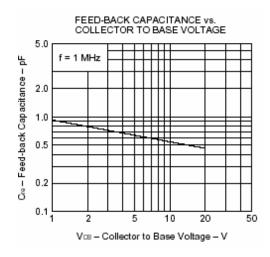


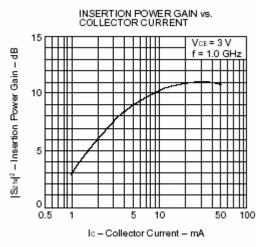


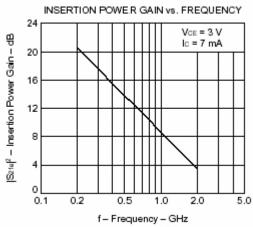
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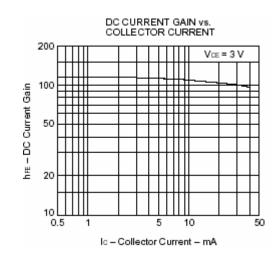














PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

